

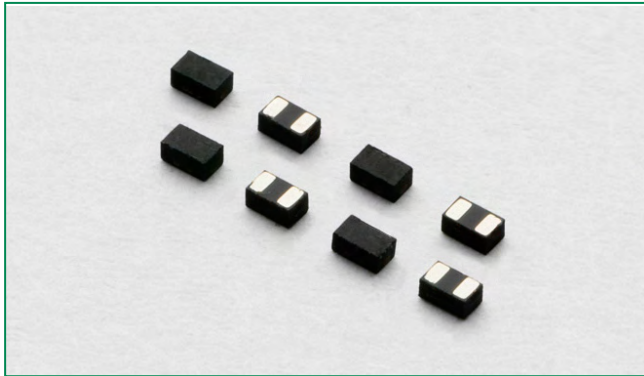
SPHV-C Series 200W Discrete Bidirectional TVS Diode



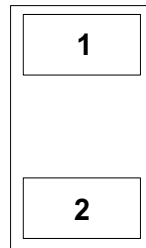
AUTOMOTIVE GRADE



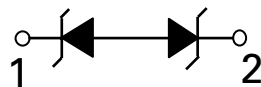
GREEN



Pinout



Functional Block Diagram



Life Support Note:

Not Intended for Use in Life Support or Life Saving Applications

The products shown herein are not designed for use in life sustaining or life saving applications unless otherwise expressly indicated.

Description

The SPHV-C series is designed to replace multilayer varistors (MLVs) in portable applications, LED lighting modules, and low speed I/Os. It will protect sensitive equipment from damage due to electrostatic discharge (ESD) and other overvoltage transients.

The SPHV-C series can safely absorb repetitive ESD strikes above the maximum level of the IEC61000-4-2 international standard (Level 4, $\pm 8\text{kV}$ contact discharge) without performance degradation and safely dissipate up to 8A (SPHV12-C) of induced surge current (IEC61000-4-5, $t_p=8/20\mu\text{s}$) with very low clamping voltages.

Features

- ESD, IEC61000-4-2, $\pm 30\text{kV}$ contact, $\pm 30\text{kV}$ air
- EFT, IEC61000-4-4, 40A (5/50ns)
- Lightning, IEC61000-4-5, 8A ($t_p=8/20\mu\text{s}$, SPHV12-C)
- Low clamping voltage
- Low leakage current
- Small SOD882 packaging helps save board space
- AEC-Q101 qualified
- Side exposed leadframe helps to verify solderability (SPHVxx-KTG-C series)

Applications

- LED Lighting Modules
- Portable Instrumentation
- General Purpose I/O
- Mobile & Handhelds
- RS232 / RS485
- CAN and LIN Bus

Additional Information



Datasheet



Resources



Samples

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
P_{pk}	Peak Pulse Power ($t_p=8/20\mu s$)	200	W
T_{OP}	Operating Temperature	-40 to 125	°C
T_{STOR}	Storage Temperature	-55 to 150	°C

Notes:

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Thermal Information

Parameter	Rating	Units
Storage Temperature Range	-55 to 150	°C
Maximum Junction Temperature	150	°C
Maximum Lead Temperature (Soldering 20-40s)	260	°C

SPHV12-C Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			12.0	V
Reverse Breakdown Voltage	V_{BR}	$I_R = 1mA$	13.3			V
Leakage Current	I_{LEAK}	$V_R = 12V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A, t_p=8/20\mu s, Fwd$			19.0	V
		$I_{PP}=8A, t_p=8/20\mu s, Fwd$			25.0	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to GND		0.48		Ω
Peak Pulse Current	I_{PP}	$t_p=8/20\mu s$			8.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact Discharge)	± 30			kV
		IEC61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	C_{D-GND}	Reverse Bias=0V, $f=1MHz$			30	pF

Note:

¹ Parameter is guaranteed by design and/or device characterization.

² Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

SPHV15-C Electrical Characteristics ($T_{OP}=25^{\circ}C$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V_{RWM}	$I_R \leq 1\mu A$			15.0	V
Reverse Breakdown Voltage	V_{BR}	$I_R = 1mA$	16.7			V
Leakage Current	I_{LEAK}	$V_R = 15V$			1.0	μA
Clamp Voltage ¹	V_C	$I_{PP}=1A, t_p=8/20\mu s, Fwd$			22.0	V
		$I_{PP}=5A, t_p=8/20\mu s, Fwd$			30.0	V
Dynamic Resistance ²	R_{DYN}	TLP, $t_p=100ns$, I/O to GND		0.43		Ω
Peak Pulse Current	I_{PP}	$t_p=8/20\mu s$			5.0	A
ESD Withstand Voltage ¹	V_{ESD}	IEC61000-4-2 (Contact Discharge)	± 30			kV
		IEC61000-4-2 (Air Discharge)	± 30			kV
Diode Capacitance ¹	$C_{I/O-GND}$	Reverse Bias=0V, $f=1MHz$			24	pF

Note:

¹ Parameter is guaranteed by design and/or device characterization.

² Transmission Line Pulse (TLP) with 100ns width and 200ps rise time.

SPHV24-C Electrical Characteristics (T_{OP}=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			24.0	V
Reverse Breakdown Voltage	V _{BR}	I _R = 1 mA	26.7			V
Leakage Current	I _{LEAK}	V _R = 24 V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1 A, t _p = 8/20 μs, Fwd			36.0	V
		I _{PP} = 3 A, t _p = 8/20 μs, Fwd			50.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p = 100 ns, I/O to GND		0.65		Ω
Peak Pulse Current	I _{PP}	t _p = 8/20 μs			3.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±24			kV
		IEC61000-4-2 (Air Discharge)	±30			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias = 0 V, f = 1 MHz			17	pF

Note:

¹ Parameter is guaranteed by design and/or device characterization.

² Transmission Line Pulse (TLP) with 100 ns width and 200 ps rise time.

SPHV36-C Electrical Characteristics (T_{OP}=25°C)

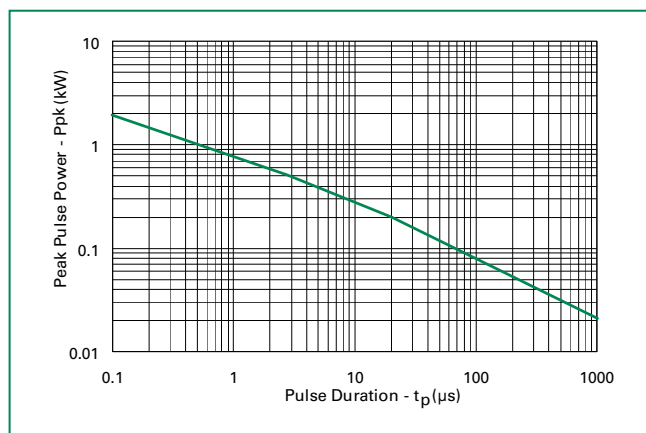
Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤ 1 μA			36.0	V
Reverse Breakdown Voltage	V _{BR}	I _R = 1 mA	40.0			V
Leakage Current	I _{LEAK}	V _R = 36 V			1.0	μA
Clamp Voltage ¹	V _C	I _{PP} = 1 A, t _p = 8/20 μs, Fwd			52.0	V
		I _{PP} = 2 A, t _p = 8/20 μs, Fwd			65.0	V
Dynamic Resistance ²	R _{DYN}	TLP, t _p = 100 ns, I/O to GND		1.33		Ω
Peak Pulse Current	I _{PP}	t _p = 8/20 μs			2.0	A
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Contact Discharge)	±15			kV
		IEC61000-4-2 (Air Discharge)	±20			kV
Diode Capacitance ¹	C _{I/O-GND}	Reverse Bias = 0 V, f = 1 MHz			13	pF

Note:

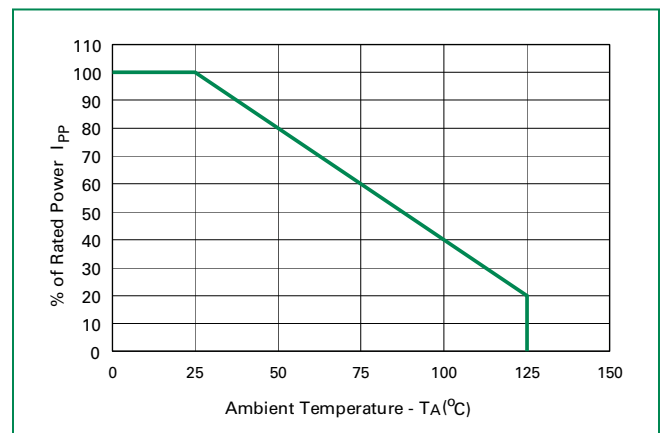
¹ Parameter is guaranteed by design and/or device characterization.

² Transmission Line Pulse (TLP) with 100 ns width and 200 ps rise time.

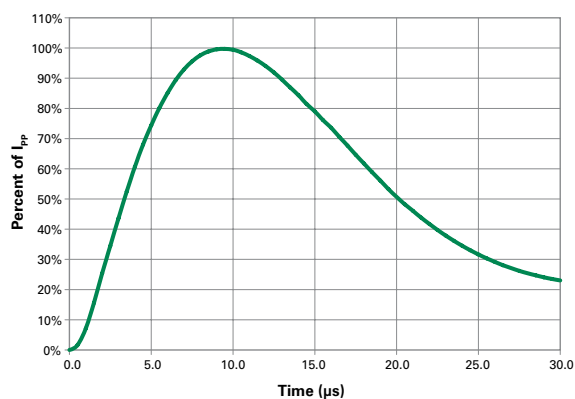
Non-Repetitive Peak Pulse Power vs. Pulse Time



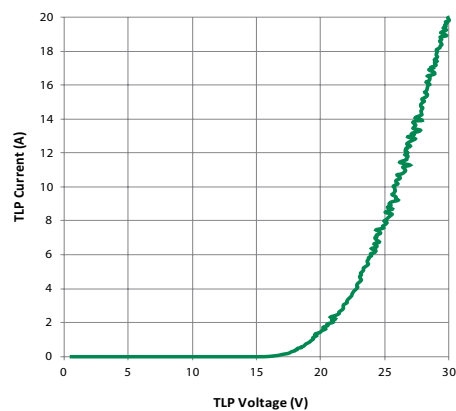
Power Derating Curve



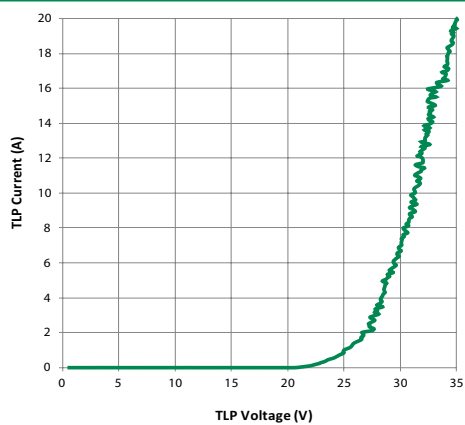
Pulse Waveform



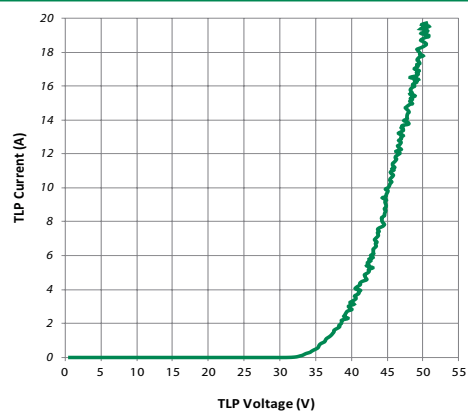
SPHV12-C Transmission Line Pulsing(TLP) Plot



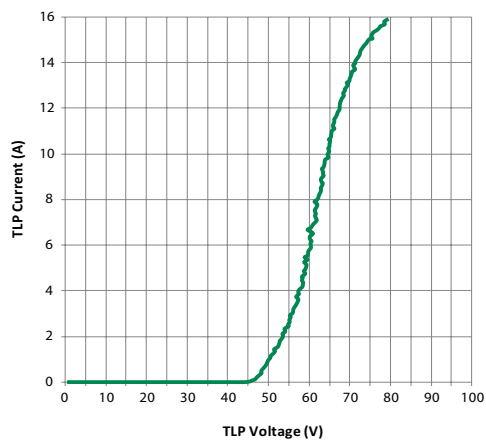
SPHV15-C Transmission Line Pulsing(TLP) Plot



SPHV24-C Transmission Line Pulsing(TLP) Plot

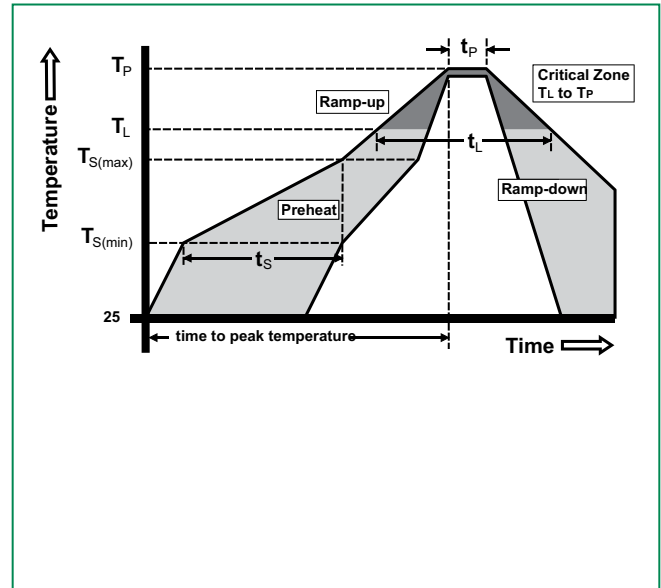


SPHV36-C Transmission Line Pulsing(TLP) Plot



Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ($T_{s(min)}$)	150°C
	- Temperature Max ($T_{s(max)}$)	200°C
	- Time (min to max) (t_s)	60 – 180 secs
Average ramp up rate (Liquidus) Temp (T_L) to peak		3°C/second max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/second max
Reflow	- Temperature (T_L) (Liquidus)	217°C
	- Temperature (t_L)	60 – 150 seconds
Peak Temperature (T_p)		260 ^{+0/-5} °C
Time within 5°C of actual peak Temperature (t_p)		20 – 40 seconds
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature (T_p)		8 minutes Max.
Do not exceed		260°C



Product Characteristics

Lead Plating	Pre-Plated Frame
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Substitute Material	Silicon
Body Material	Molded Epoxy
Flammability	UL 94 V-0

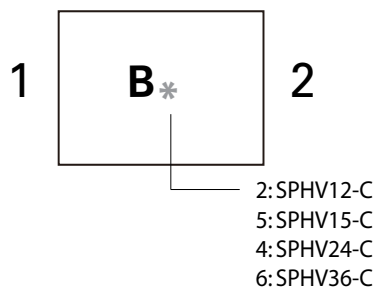
Notes :

1. All dimensions are in millimeters
2. Dimensions include solder plating.
3. Dimensions are exclusive of mold flash & metal burr.
4. Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
5. Package surface matte finish VDI 11-13.

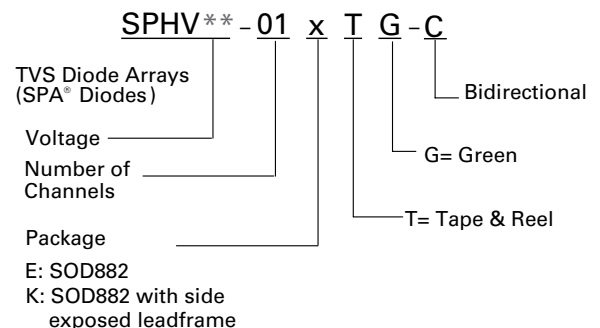
Ordering Information

Part Number	Package	Marking	Min. Order Qty.
SPHV12-01ETG-C	SOD882	B2	10000
SPHV15-01ETG-C		B5	
SPHV24-01ETG-C		B4	
SPHV36-01ETG-C		B6	
SPHV12-01KTG-C	SOD882 with side exposed leadframe	B2	10000
SPHV15-01KTG-C		B5	
SPHV24-01KTG-C		B4	
SPHV36-01KTG-C		B6	

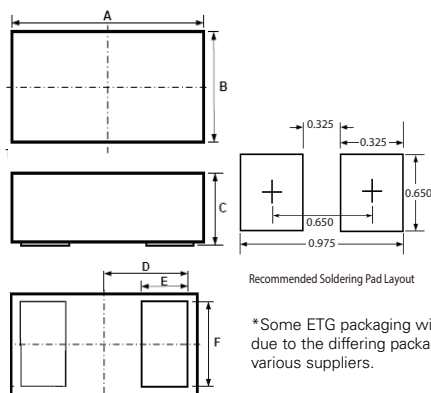
Part Marking System



Part Numbering System

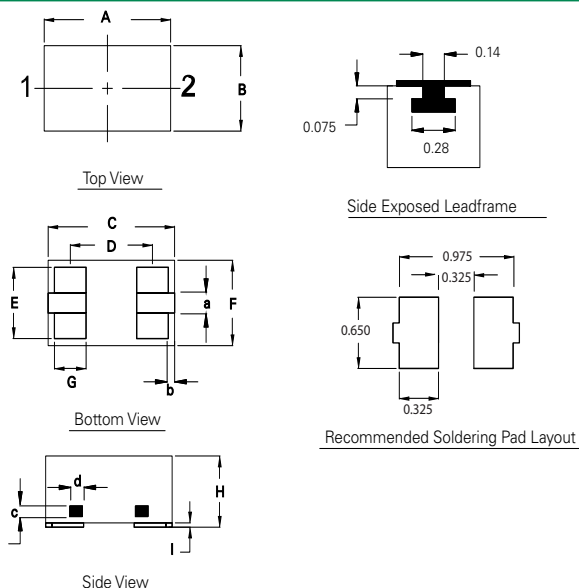


Package Dimensions — SOD882(SPHVxx-01ETG-C)



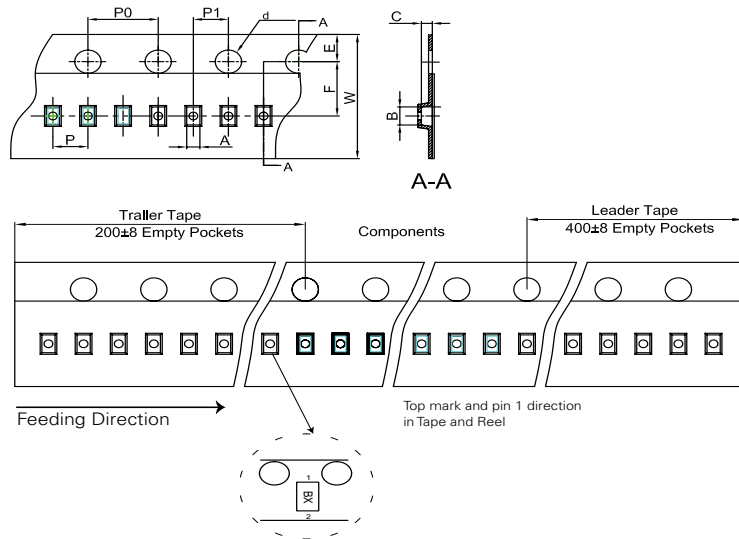
Symbol	Package	SOD882					
	JEDEC	MO-236					
	Millimeters			Inches			
	Min	Typ	Max	Min	Typ	Max	
A	0.90	1.00	1.10	0.037	0.039	0.041	
B	0.50	0.60	0.70	0.022	0.024	0.026	
C	0.40	0.50	0.60	0.016	0.020	0.024	
D	0.45			0.018			
E	0.20	0.25	0.35	0.008	0.010	0.012	
F	0.45	0.50	0.55	0.018	0.020	0.022	

Package Dimensions — SOD882 with side exposed leadframe(SPHVxx-01KTG-C)



Symbol	Package	SOD882 with side exposed leadframe					
	JEDEC	MO-236					
	Millimeters			Inches			
	Min	Typ	Max	Min	Typ	Max	
A	0.90	1.00	1.10	0.037	0.039	0.043	
B	0.50	0.60	0.70	0.020	0.024	0.028	
C	0.90	1.00	1.10	0.037	0.039	0.043	
D	0.55	0.65	0.75	0.022	0.026	0.030	
E	0.40	0.50	0.60	0.016	0.020	0.024	
F	0.50	0.60	0.70	0.020	0.024	0.028	
G	0.20	0.25	0.30	0.008	0.010	0.012	
H	0.40	0.50	0.60	0.016	0.020	0.024	
I	0.05 max			0.002 max			
a	-	0.14	-	-	0.006	-	
b	-	0.04	-	-	0.002	-	
c	-	0.075	-	-	0.003	-	
d	-	0.10	-	-	0.004	-	

Embossed Carrier Tape & Reel Specification



Symbol	Millimeters
A	0.70+/-0.045
B	1.10+/-0.045
C	0.65+/-0.045
d	1.55+/-0.10
E	1.75+/-0.05
F	3.50+/-0.05
P	2.00+/-0.10
P0	4.00+/-0.10
P1	2.00+/-0.10
W	8.00 + 0.30 -0.10

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

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Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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